Amendments to the Specification:

Please replace paragraph **[0072]** with the following rewritten paragraph:

[0072] Now, a material disposing process of the exemplary embodiment will be described. The material disposing process is a process to form a film pattern (a wiring pattern) having a shape of line on the substrate P by ejecting the liquid droplets 30 of the functional solution containing a wiring pattern formation material from the liquid droplet ejection head 1 of the liquid droplet ejection apparatus to dispose the liquid droplets in the grooves 34 between the banks B and B as shown in ~~Fig. 7e and 7f~~ Figs. 7a and 7b. In the exemplary embodiment, the functional solution includes an organic silver compound dispersed in tetradecane, serving as a dispersing medium.

Please replace paragraph **[0075]** with the following rewritten paragraph:

[0075] After the liquid droplets are ejected on the substrate P, a drying process is performed in order to remove the dispersing media and ensure thickness of the film, if necessary. The drying process may employ, for example, a lamp annealing process as well as a general process using hot plates, electric furnaces, or the like, to heat the substrate P. A light source used for the lamp annealing process includes, but is not limited to, an infrared lamp, a xenon lamp, a YAG laser, an argon laser, a carbon dioxide laser, an excimer laser using XeF, XeCl, XeBr, KrF, KrCl, ArF, ArCl, etc. Although the powers of these lasers are generally in a range of 10 to 5000 W, the laser of the present exemplary embodiment satisfactorily utilizes the power of 100 to 1000 W. A plurality of liquid droplets of the functional solution are stacked to form a plurality of films by repetition of the intermediate drying process and the material disposing process, as shown in Fig. ~~7g~~ 7c, so that the wiring pattern (the film pattern) 33A having a large thickness can be formed.

Please replace paragraph **[0077]** with the following rewritten paragraph:

[0077] For this reason, a thermal treatment and/or ~~a~~ an optical treatment are

performed on the substrate after the ejection process. Although the thermal treatment and/or the optical treatment are generally performed at the atmosphere, it may be performed at an inert gas ambiance using nitrogen, argon, helium, etc., if necessary. The process temperature of the thermal treatment and/or the optical treatment is suitably selected in consideration of a boiling point (a vapor pressure) of a dispersing medium, types or pressure of ambient gas, a dispersibility of micro-particles, an organic silver compound, thermal behaviors, such as an oxidation property, presence or absence of a coating material, and an amount of the coating material, heat-resistant temperature of a base material, etc. For example, a firing process is necessarily performed at about 200° C to remove organic materials of the organic silver compound. In case of the substrate being made of plastic, the firing process may be performed at a temperature of the room temperature to 100° C. According to the foregoing process, the conductive materials (the organic silver compound) after the ejection process are transformed into a conductive film (the wiring pattern) 33 due to the remaining silver particles, as shown in Fig. ~~7h~~ 7d.